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STB13NK60ZT4, STP13NK60Z STP13NK60ZFP, STW13NK60Z

N-channel 600 V, 0.48 Ω , 13 A, TO-220, TO-220FP, D²PAK
TO-247 Zener-protected SuperMESH™ Power MOSFET

Features

Type	V _{DSS}	R _{DS(on)} max	I _D	P _w
STB13NK60ZT4	600 V	<0.55 Ω	13 A	150 W
STP13NK60ZFP	600 V	<0.55 Ω	13 A	35 W
STP13NK60Z	600 V	<0.55 Ω	13 A	150 W
STW13NK60Z	600 V	<0.55 Ω	13 A	150 W

- Gate charge minimized
- Very low intrinsic capacitances
- Very good manufacturing repeatability

Application

- Switching applications

Description

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications.

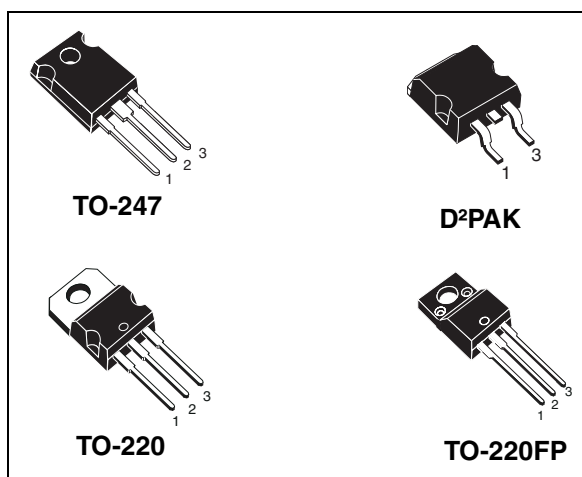


Figure 1. Internal schematic diagram

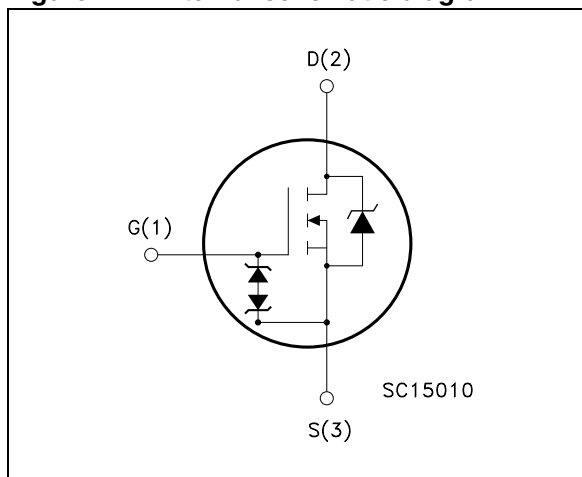


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB13NK60ZT4	B13NK60Z	D ² PAK	Tape and reel
STP13NK60ZFP	P13NK60ZFP	TO-220FP	Tube
STP13NK60Z	P13NK60Z	TO-220	Tube
STW13NK60Z	W13NK60Z	TO-247	Tube

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STB13NK60ZT4, STx13NK60Z, STP13NK60ZFP

Electrical ratings

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220 / TO-247 D ² PAK	TO-220FP	
V _{DS}	Drain-source voltage (V _{GS} = 0)	600		V
V _{GS}	Gate-source voltage	± 30		V
I _D	Drain current (continuous) at T _C = 25 °C	13	13 ⁽¹⁾	A
I _D	Drain current (continuous) at T _C = 100 °C	8.2	8.2 ⁽¹⁾	A
I _{DM} ⁽²⁾	Drain current (pulsed)	52	52 ⁽¹⁾	A
P _{TOT}	Total dissipation at T _C = 25 °C	150	35	W
	Derating factor	1.20	0.27	W/°C
Vesd(G-S)	G-S ESD (HBM C=100pF, R=1.5 kΩ)	4000		V
dv/dt ⁽³⁾	Peak diode recovery voltage slope	4.5		V/ns
V _{ISO}	Insulation withstand voltage (AC)	--	2500	V
T _j T _{stg}	Operating junction temperature Storage temperature	-55 to 150		°C

1. Limited only by maximum temperature allowed
2. Pulse width limited by safe operating area
3. I_{SD} ≤ 13 A, di/dt ≤ 200 A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ T_{JMAX}

Table 3. Thermal data

Symbol	Parameter	Value			Unit
		TO-220 TO-247	D ² PAK	TO-220FP	
R _{thj-case}	Thermal resistance junction-case max	0.83		3.6	°C/W
R _{thj-pcb} ⁽¹⁾	Thermal resistance junction-pcb max	--	60	--	°C/W
R _{thj-amb}	Thermal resistance junction-amb max	62.5			°C/W
T _l	Maximum lead temperature for soldering purpose	300			°C

1. When mounted on minimum footprint

Electrical ratings

STB13NK60ZT4, STx13NK60Z, STP13NK60ZFP

Table 4. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	10	A
E_{AS}	Single pulse avalanche energy (starting $T_j=25\text{ }^{\circ}\text{C}$, $I_D=I_{AR}$, $V_{DD}=50\text{ V}$)	400	mJ

STB13NK60ZT4, STx13NK60Z, STP13NK60ZFP

Electrical characteristics

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Figure 2. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	I _D = 1 mA, V _{GS} = 0	600			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V _{DS} = Max rating, V _{DS} = Max rating, T _c = 125 °C			1 50	μA μA
I _{GSS}	Gate body leakage current (V _{DS} = 0)	V _{GS} = ±20 V			±10	μA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 100 μA	3	3.75	4.5	V
R _{DS(on)}	Static drain-source on resistance	V _{GS} = 10 V, I _D = 4.5 A		0.48	0.55	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g _{fs} ⁽¹⁾	Forward transconductance	V _{DS} = 8 V, I _D = 5 A	-	11		S
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V _{DS} = 25 V, f = 1 MHz, V _{GS} = 0	-	2030 210 48		pF pF pF
C _{oss eq.} ⁽²⁾	Equivalent output capacitance	V _{GS} = 0, V _{DS} = 0 to 480 V	-	125		pF
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	V _{DD} = 480 V, I _D = 10 A V _{GS} = 10 V (see Figure 21)	-	66 11 33	92	nC nC nC

1. Pulsed: pulse duration = 300 μs, duty cycle 1.5%

2. C_{oss eq.} is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Electrical characteristics

STB13NK60ZT4, STx13NK60Z, STP13NK60ZFP

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD}=300\text{ V}$, $I_D=5\text{ A}$, $R_G=4.7\ \Omega$, $V_{GS}=10\text{ V}$ (see Figure 20)	-	22	-	ns
t_r	Rise time			14		ns
$t_{d(off)}$	Turn-off delay time	$V_{DD}=300\text{ V}$, $I_D=5\text{ A}$, $R_G=4.7\ \Omega$, $V_{GS}=10\text{ V}$ (see Figure 20)	-	61	-	ns
t_f	Fall time			12		ns
$t_{r(Voff)}$	Off-voltage rise time	$V_{DD}=480\text{ V}$, $I_D=10\text{ A}$, $R_G=4.7\ \Omega$, $V_{GS}=10\text{ V}$ (see Figure 20)	-	10	-	ns
t_f	Fall time			9		ns
t_c	Cross-over time			20		ns

Table 7. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
BV_{GSO}	Gate-source breakdown voltage	$I_{GS}=\pm 1\text{ mA}$ (open drain)	30	-	-	V

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		10	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				40	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=10\text{ A}$, $V_{GS}=0$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD}=10\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$, $V_{DD}=35\text{ V}$, $T_J=150\text{ }^\circ\text{C}$	-	570		ns
Q_{rr}	Reverse recovery charge			4.5		μC
I_{RRM}	Reverse recovery current			16		A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

STB13NK60ZT4, STx13NK60Z, STP13NK60ZFP

Electrical characteristics

2.1 Electrical characteristics (curves)

Figure 3. Safe operating area for TO-220/D²PAK

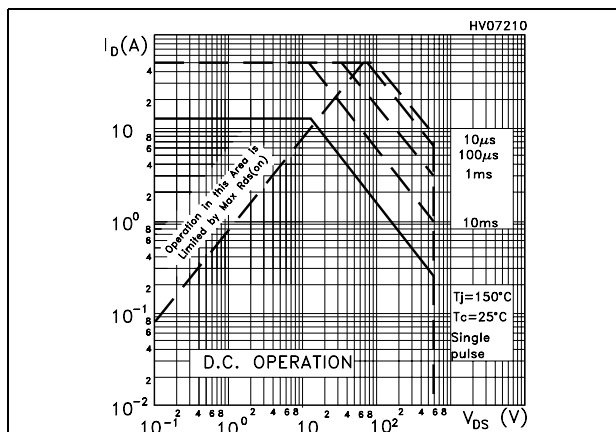


Figure 4. Thermal impedance for TO-220/D²PAK

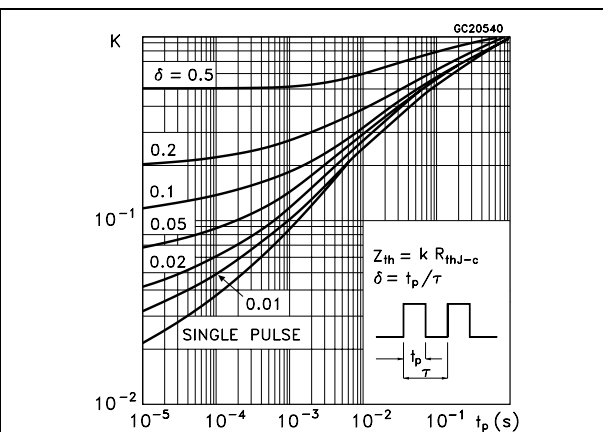


Figure 5. Safe operating area for TO-220FP

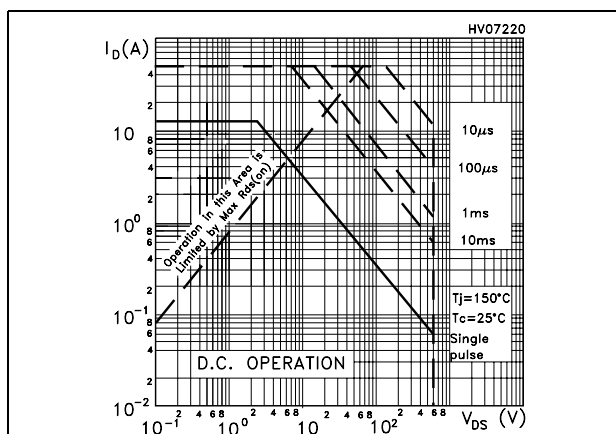


Figure 6. Thermal impedance for TO-220FP

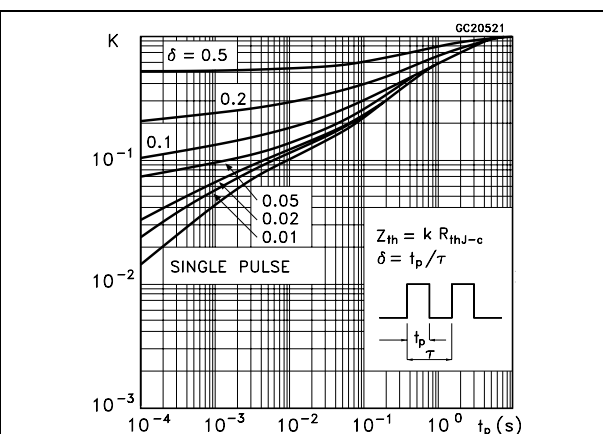


Figure 7. Safe operating area for TO-247

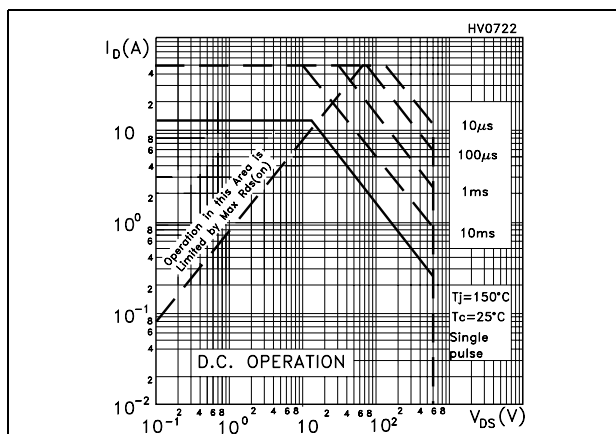
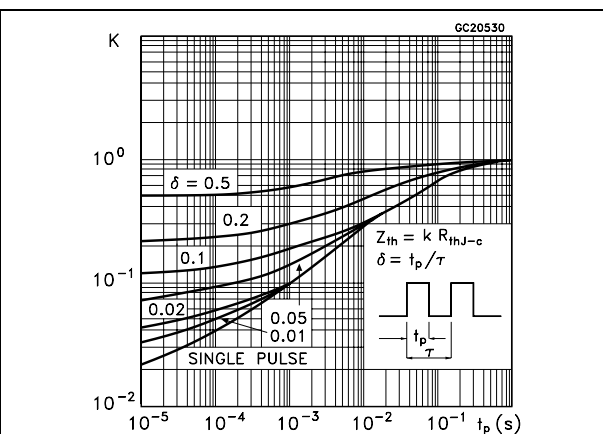


Figure 8. Thermal impedance for TO-247



Electrical characteristics

STB13NK60ZT4, STx13NK60Z, STP13NK60ZFP

Figure 9. Output characteristics

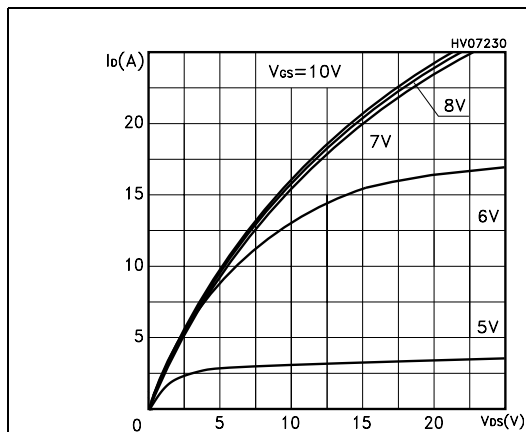


Figure 10. Transfer characteristics

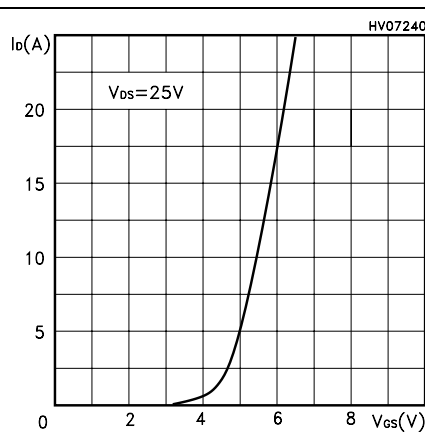


Figure 11. Transconductance

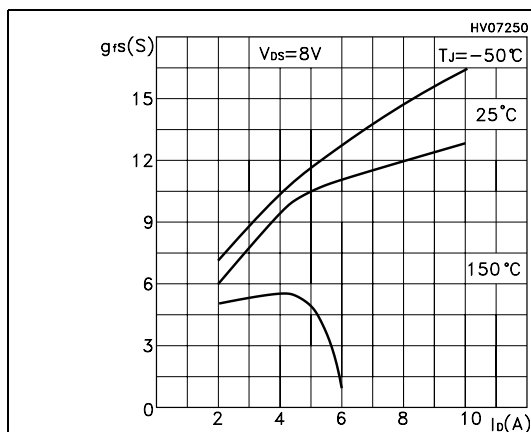


Figure 12. Static drain-source on resistance

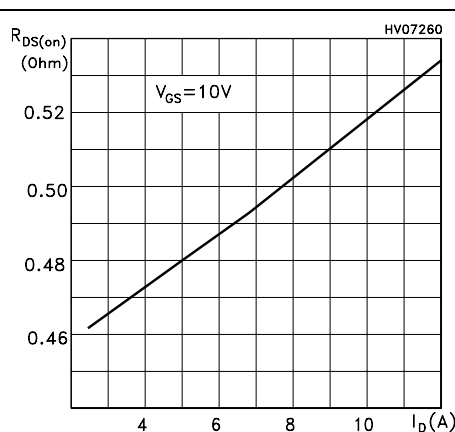


Figure 13. Gate charge vs gate-source voltage

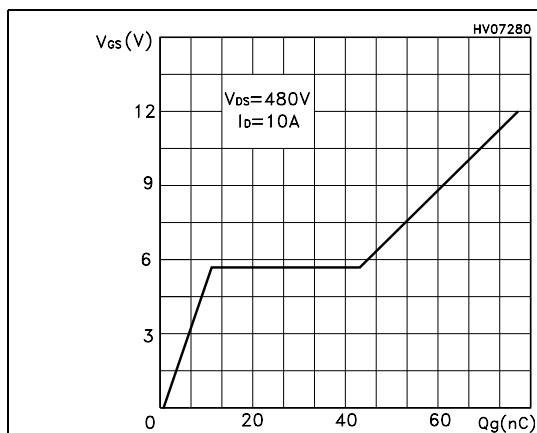
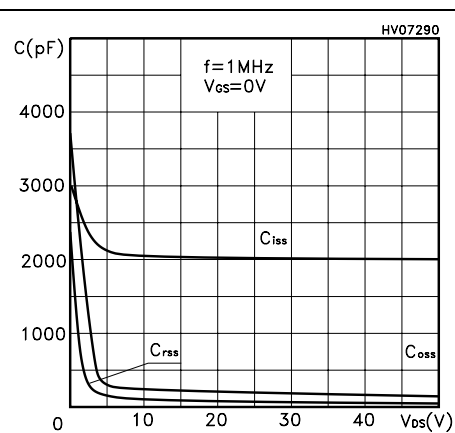


Figure 14. Capacitance variations



STB13NK60ZT4, STx13NK60Z, STP13NK60ZFP

Electrical characteristics

Figure 15. Normalized gate threshold voltage vs temperature

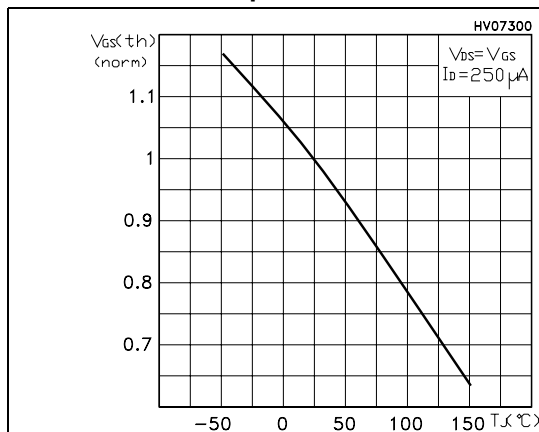


Figure 16. Normalized on resistance vs temperature

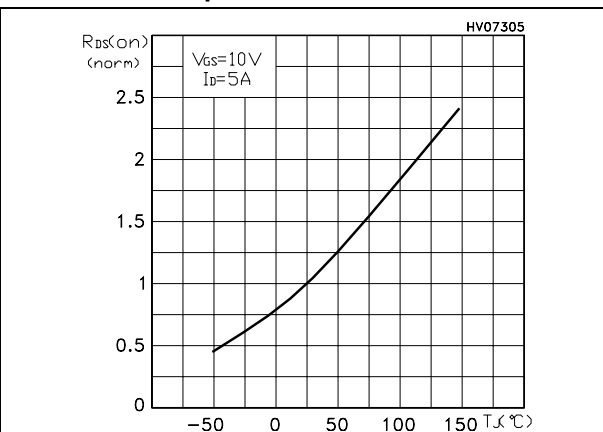


Figure 17. Source-drain diode forward characteristics

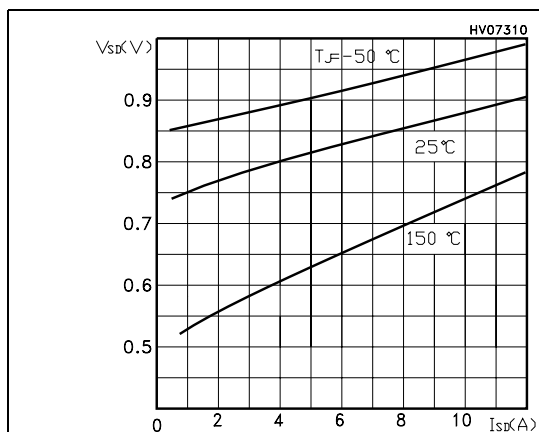


Figure 18. Normalized BV_{DSS} vs temperature

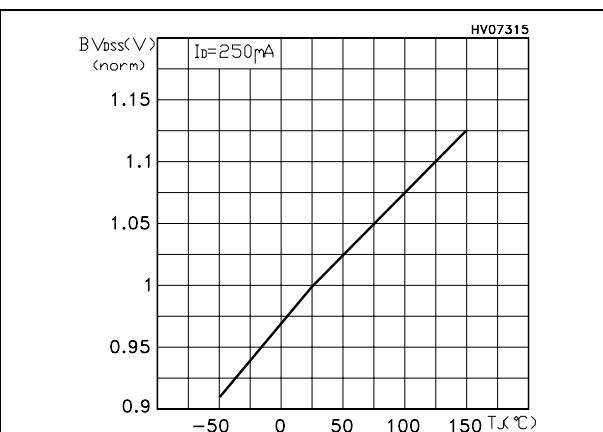
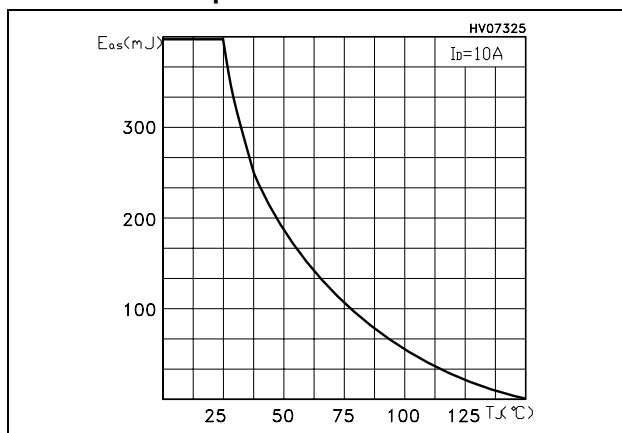


Figure 19. Maximum avalanche energy vs temperature



Test circuits

STB13NK60ZT4, STx13NK60Z, STP13NK60ZFP

3 Test circuits

Figure 20. Switching times test circuit for resistive load

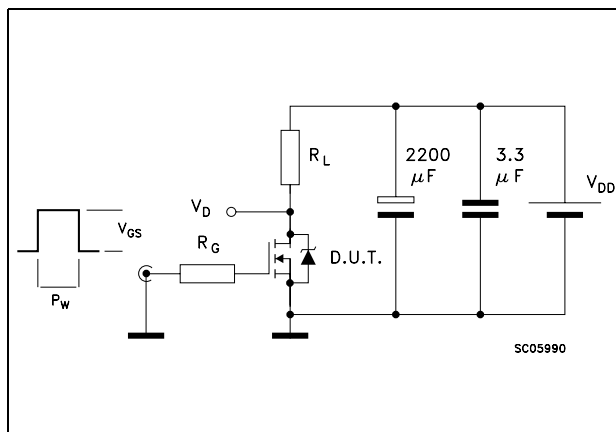


Figure 21. Gate charge test circuit

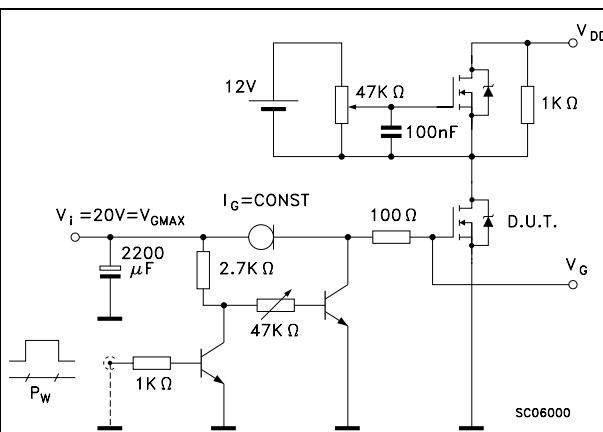


Figure 22. Test circuit for inductive load switching and diode recovery times

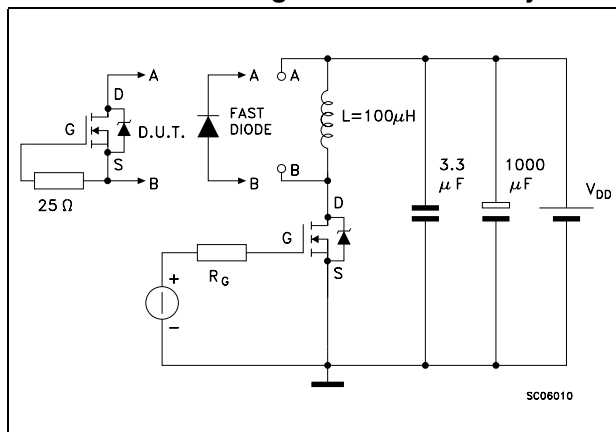


Figure 23. Unclamped inductive load test circuit

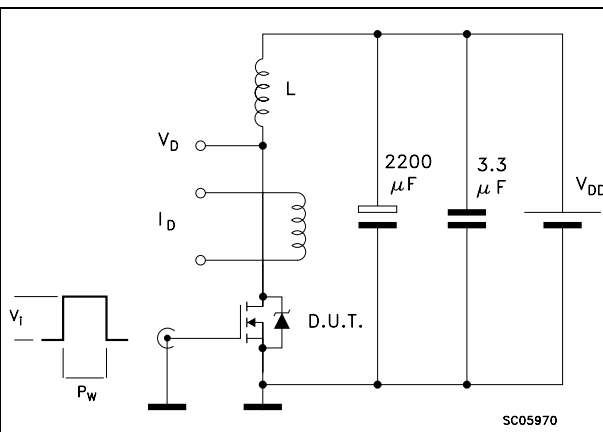


Figure 24. Unclamped inductive waveform

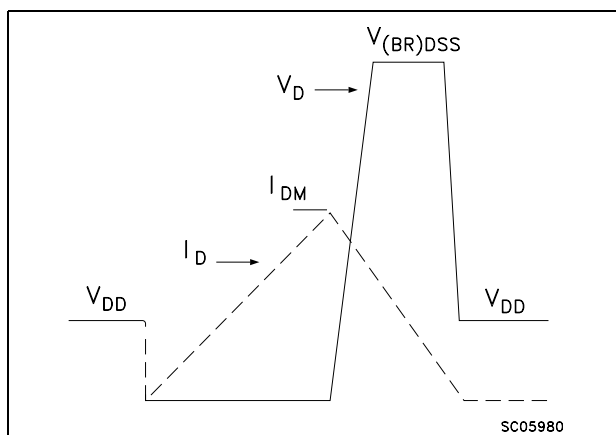
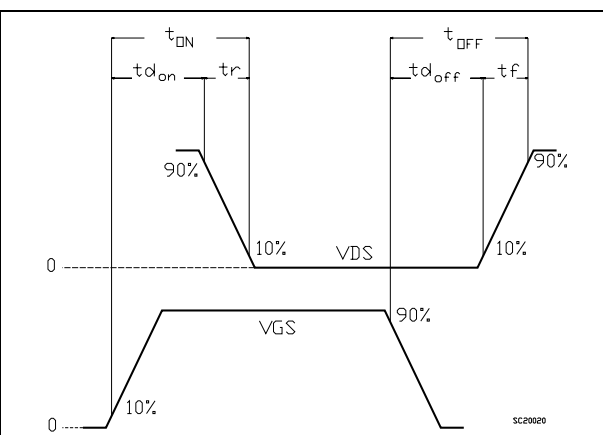


Figure 25. Switching time waveform



4 Package mechanical data

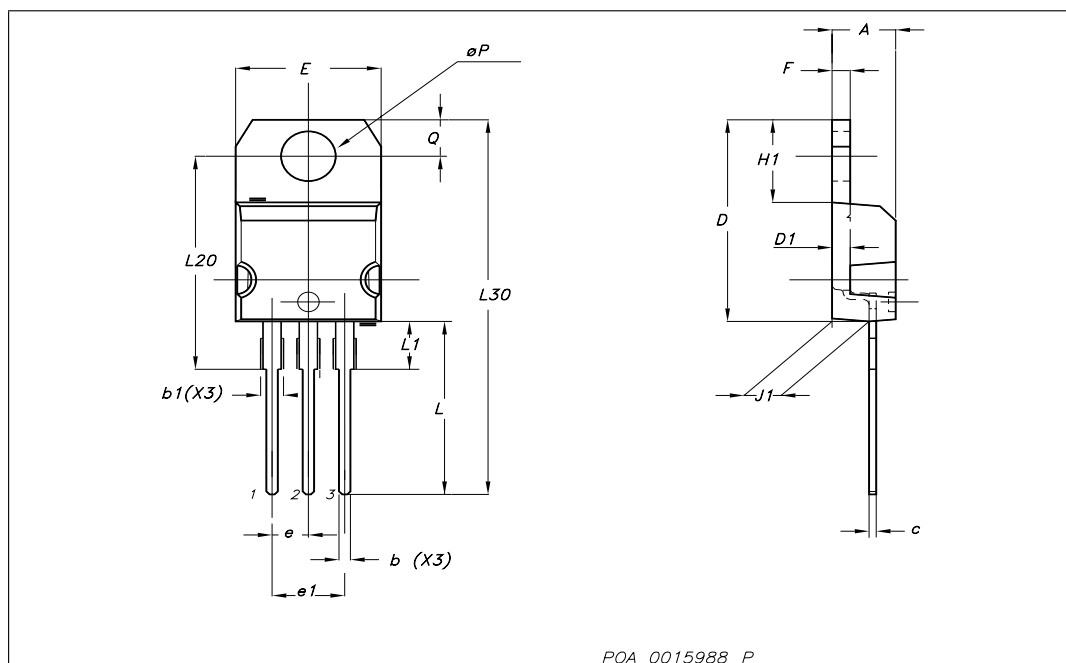
In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Package mechanical data

STB13NK60ZT4, STx13NK60Z, STP13NK60ZFP

TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ØP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116

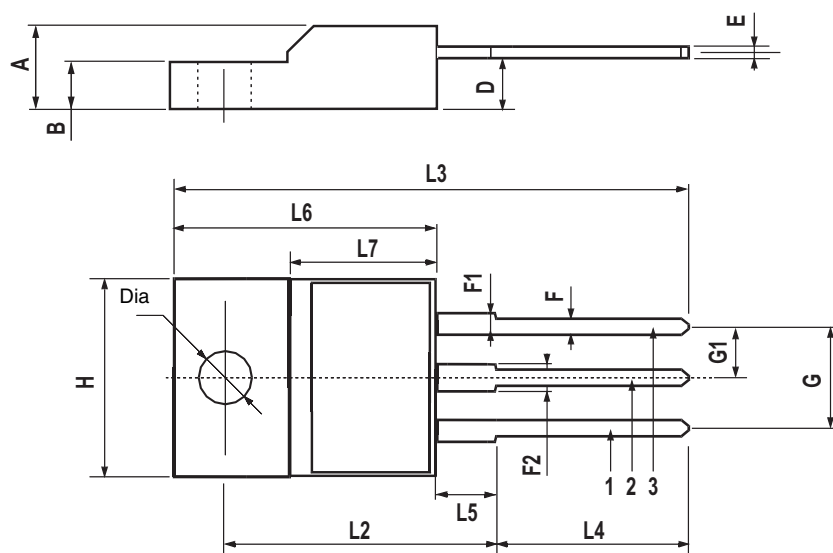


STB13NK60ZT4, STx13NK60Z, STP13NK60ZFP

Package mechanical data

TO-220FP mechanical data

Dim.	mm.			inch		
	Min.	Typ	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.70	0.017		0.027
F	0.75		1.00	0.030		0.039
F1	1.15		1.50	0.045		0.067
F2	1.15		1.50	0.045		0.067
G	4.95		5.20	0.195		0.204
G1	2.40		2.70	0.094		0.106
H	10		10.40	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.80		10.60	0.385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.90		16.40	0.626		0.645
L7	9		9.30	0.354		0.366
Dia	3		3.2	0.118		0.126

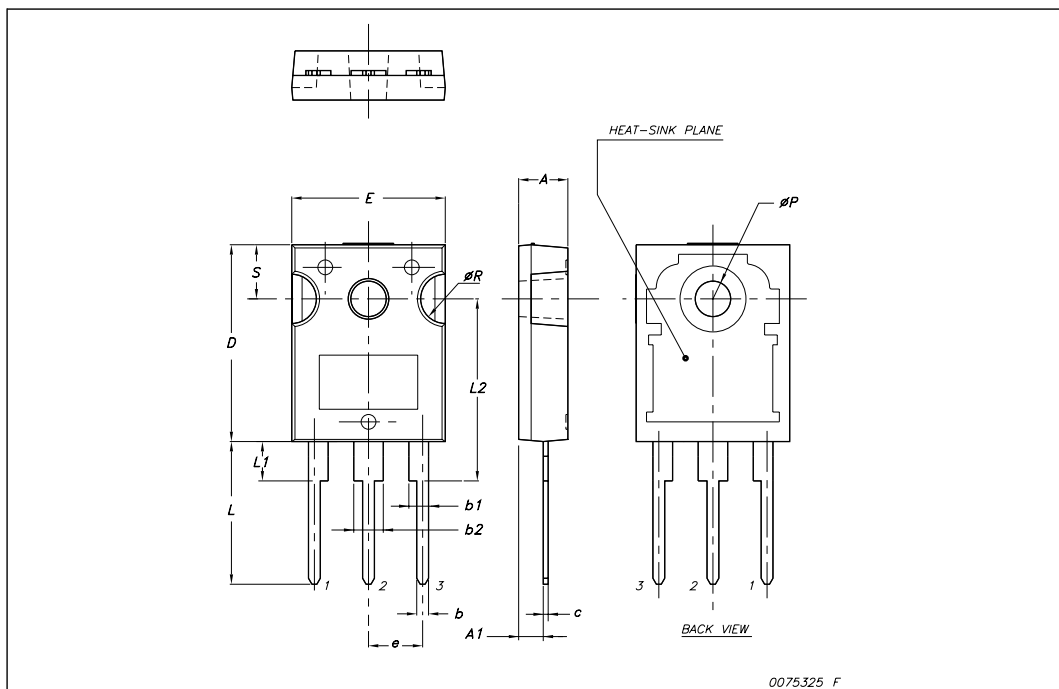


Package mechanical data

STB13NK60ZT4, STx13NK60Z, STP13NK60ZFP

TO-247 Mechanical data

Dim.	mm.		
	Min.	Typ	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
øP	3.55		3.65
øR	4.50		5.50
S		5.50	

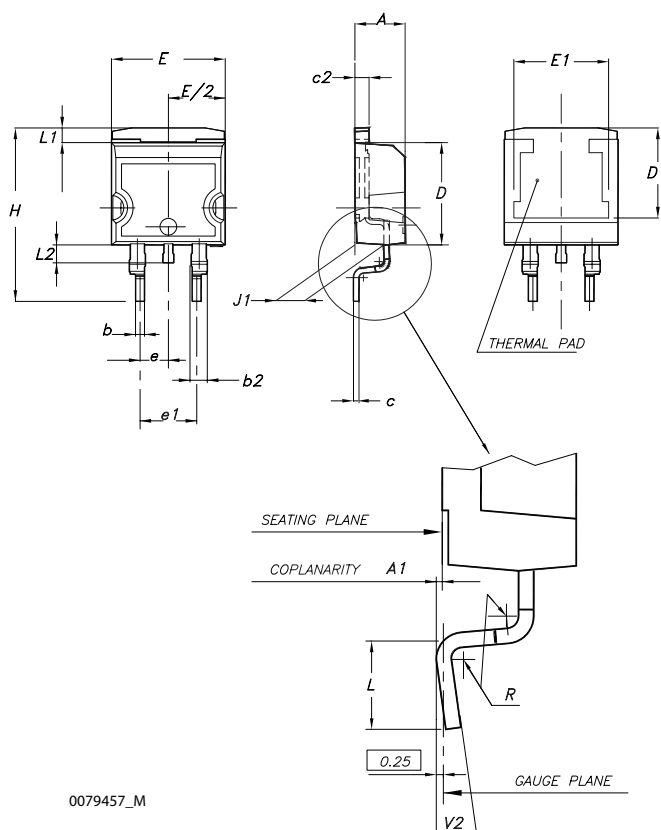


STB13NK60ZT4, STx13NK60Z, STP13NK60ZFP

Package mechanical data

D²PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°



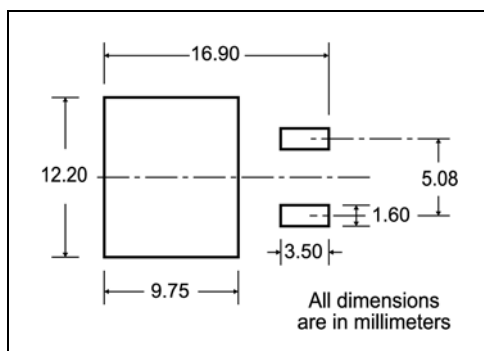
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Packing mechanical data

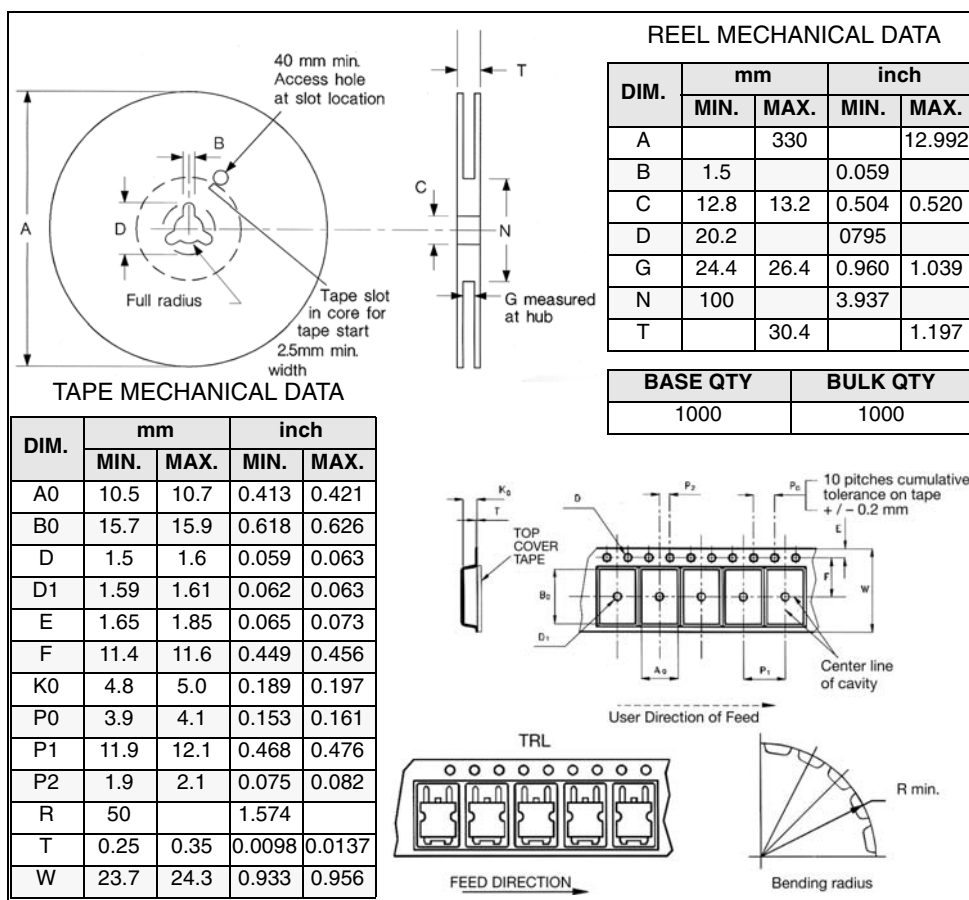
STB13NK60ZT4, STx13NK60Z, STP13NK60ZFP

5 Packing mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



* on sales type

6 Revision history

Table 9. Document revision history

Date	Revision	Changes
20-Sep-2005	4	
05-Oct-2005	5	Inserted ECOPACK [®] indication
29-Feb-2008	6	V _{ISO} parameter on Table has been updated
15-Apr-2009	7	Order codes in Table 1: Device summary has been changed

STB13NK60ZT4, STx13NK60Z, STP13NK60ZFP

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